SSDM 2000

Advanced Program Part 2
(Late News etc.)

LATE NEWS PAPERS

August 29, Tuesday

Room D

15:15 LD-1-1 A Vertical, MOS-Based Silicon Tunneling Transistor
W. Hansch, J. Schulze*, C. Fink* and I. Eisele*
*Technical Univ. of Munich and *Univ. of the German Federal Armed Forces, Germany*

Room E

17:30 LE-1-1 Very-Large-Gain Collector-up GaN/W/WO_3 Metal Base Transistors
K. Mochizuki, K. Uesugi*, P.M. Asbeck**, J. Gotoh, T. Mishima, K. Hirata*** and H. Oda***
*Hitachi, *Hokkaido Univ., Japan, **Univ. of California, USA and ***Hitachi ULSI Systems, Japan*

17:45 LE-1-2 Recessed Gate AlGaN/GaN HEMT on Sapphire Grown by MOCVD
T. Egawa, H. Ishikawa, G. Zhao and M. Umeno
Nagoya Inst. of Technol., Japan

August 30, Wednesday

Room B

11:15 LB-1-1 Plasma Charging Damage Immunity in SOI Devices
M. Khare, A. Mocuta, E. Leobandung, T. Chou, B. Linder, W. Rausch, P. Agnello, F. Assaderaghi, L.T. Su, G. Shahidi and T.-C. Chen
IBM, USA

11:30 LB-1-2 Reduction of R_{on} in Vertical Power-MOSFETs due to Local Channel Doping
C. Fink, J. Schulze, I. Eisele, W. Hansch*, W. Werner** and W. Kanert**
*Univ. of the German Federal Armed Forces, *Technical Univ. of Munich and **Infineon Technols., Germany*

Room C

16:45 LC-1-1 Endurance Enhancement in *micro*FLASHR® Memory Device
E. Aloni, M. Gutman, Y. Roizin, D. Finzi, C.I. Hyun, *I. Bloom, *D. Levy, *A. Larinn and *P. Pavan
*Tower Semiconductor and *Saifun Semiconductor, Israel*

17:00 LC-1-2 Evaluation of $SrBi_2(Ta_xNb_{1-x})_2O_9$(SBTN) Crystallization Technique at 650°C
K. Nakamura, H. Yamawaki and S. Otani
Fujitsu Labs., Japan

17:15 LC-1-3 Fabrication and Characterization of Pt/(Bi, La)$_4Ti_3O_{12}/Si_3N_4$/Si MFIS Structure for FET-Type Ferroelectric Memory Applications
T. Kijima, Y. Fujisaki and H. Ishiwara
Tokyo Inst. of Technol., Japan

August 31, Thursday

Room B

11:45 LB-2-1 Spectroscopic Ellipsometry for the Identification of Paracrystallites in the Ultra-Thin Thermal CVD Hydrogenated Amorphous Silicon Films
S. Hazra, I. Sakata, M. Yamanaka and E. Suzuki
ETL, Japan

Room C

12:15 LC-2-1 Comparison in Splitting Bonded SOI by Solid and Fluid Wedges (Water and Air Jets)
K. Sakaguchi, K. Yanagita, H. Kurisu, H. Suzuki, K. Ohmi and T. Yonehara
Canon, Japan

Room E

13:30 LE-2-1 Intrinsic Gettering In Nitrogen Doped and Hydrogen Annealed Czochralski-Grown Silicon Wafers
H. Goto, L.-S. Pan, M. Tanaka and K. Kashima
Toshiba Ceramics, Japan

13:45 LE-2-2 Performance of Submicron Large-Grain Polysilicon-on-Insulator (LPSOI) MOSFETs Formed by Crystallization of Amorphous Silicon
M. Chan, H. Wang and S. Jagar
Hong Kong Univ. of Sci. & Technol., Hong Kong

14:00 LE-2-3 Investigation on Reliability of High Quality Ultra-Thin ISSG Oxides
T.Y. Luo, G.A. Brown* and A.L.P. Rotondaro**
*Univ. of Texas, *International Sematech and **Texas Instruments, USA*

14:15	LE-2-4	The Effect of Organic Compounds Contamination on the Electrical Characteristics of Ultra-Thin Gate Oxide Films Y. Wakayama, T. Ohkawa, O. Nakamura, S. Kobayashi*, S. Sugawa, H. Aharoni and T. Ohmi *Tohoku Univ. and *Taisei, Japan*
14:30	LE-2-5	Influence of Organic Contaminant on Breakdown Characteristics of MOS Capacitors with Thin SiO_2 T. Yoshino, S. Yokoyama, T. Suzuki* and T. Fujii* *Hiroshima Univ. and *EBARA, Japan*
14:45	LE-2-6	Sub-2nm Equivalent SiO_2 Thickness Ta_2O_5 for Gate Dielectric Using RTA+UV/O_3 A. Yamaguchi, T. Aoyama and T. Sugii *Fujitsu Labs., Japan*

PROGRAM CHANGE

September 22, Wednesday

Room C

14:00→15:00 C-5-2→C-5-5
The Potential of III-Nitrides for Use in High-Speed Field-Effect Trasistors
F. Schwierz and G. Gobsch, Technische Univ. Ilmenau, Germany

15:00→14:00 C-5-5→C-5-2
High-Gain Multi-Finger AlGaN/GaN HJFETs with 0.3-um Gate Length for K-and Ka-Band Applications
K. Kunihiro, K.Kasahara, Y. Takahashi and Y. Ohno, NEC, Japan

September 23, Thursday

Room B

9:00 B-8-1 (Invited) Circuits Design Technology for High Speed SOI-MPU
C. Akrout, IBM, USA